

MA4SW210B-1 MA4SW310B-1



**HMIC™ Silicon PIN Diode Switches
with Integrated Bias Network**

RoHS Compliant

Rev. V4

Features

- ◆ Broad Bandwidth Specified 2 to 18 GHz
- ◆ Usable up to 26 GHz
- ◆ Integrated Bias Network
- ◆ Low Insertion Loss / High Isolation
- ◆ Rugged,
- ◆ Fully Monolithic
- ◆ Glass Encapsulate Construction
- ◆ Polymer Protective Coating

Description

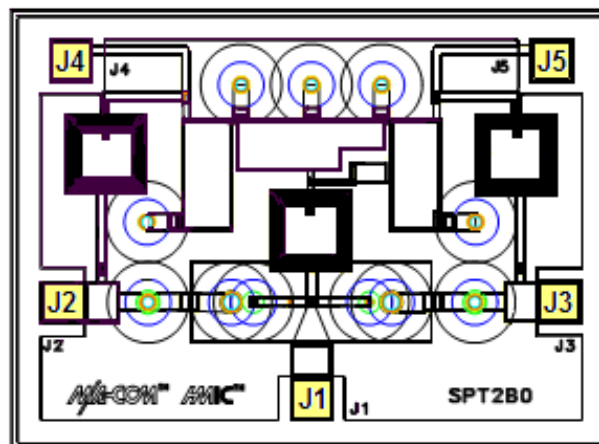
The MA4SW210B-1 and MA4SW310B-1 devices are SP2T and SP3T broad band switches with integrated bias networks utilizing M/A-COM's HMIC™ (Heterolithic Microwave Integrated Circuit) Process, US Patent 5,268,310. This process allows the incorporation of silicon pedestals that form series and shunt diodes or vias by imbedding them in low loss, low dispersion glass. By using small spacing between elements, this combination of silicon and glass gives HMIC devices low loss and high isolation performance with exceptional repeatability through low millimeter frequencies.

Large bond pads facilitate the use of low inductance ribbon bonds, while gold backside metallization allows for manual or automatic chip bonding via 80Au/20Sn, Sn62/Pb36/Ag2 solders or electrically conductive silver epoxy.

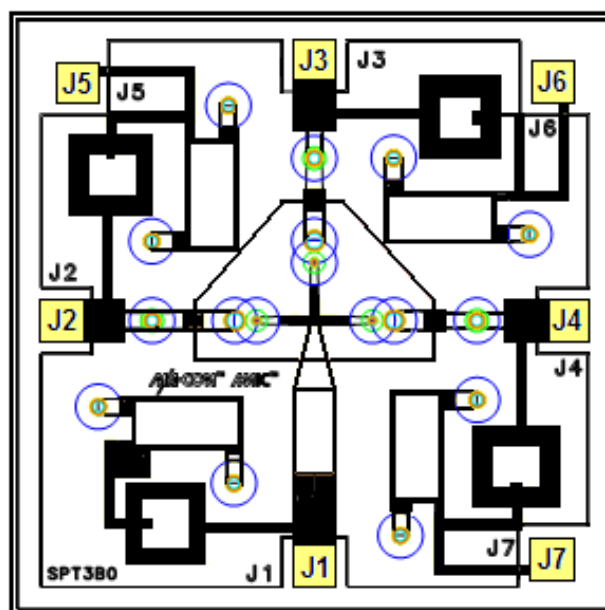
Parameter	Absolute Maximum
Operating Temperature	-65°C to +125°C
Storage Temperature	-65°C to +150°C
Junction Temperature	+175°C
Applied Reverse Voltage	- 50V
RF C.W. Incident Power	+30dBm C.W.
Bias Current +25°C	± 20mA

**Max. operating conditions for a combination of
RF power, D.C. bias and temperature:
+30dBm CW @ 15mA (per diode) @+85°C**

MA4SW210B-1



MA4SW310B-1



Yellow areas indicate bond pads

MA4SW210B-1 (SPDT)
Electrical Specifications @ T_{AMB} = +25°C, 20mA Bias current

Parameter	Frequency	Minimum	Nominal	Maximum	Units
Insertion Loss	2 GHz		1.5	1.8	dB
	6 GHz		0.70	1.0	dB
	12 GHz		0.90	1.2	dB
	18 GHz		1.2	1.8	dB
Isolation	2 GHz	55	60		dB
	6 GHz	47	50		dB
	12 GHz	40	45		dB
	18 GHz	36	40		dB
Input Return Loss	2 GHz		14		dB
	6 GHz		15		dB
	12 GHz		15		dB
	18 GHz		13.0		dB
Switching Speed¹	-		50		ns

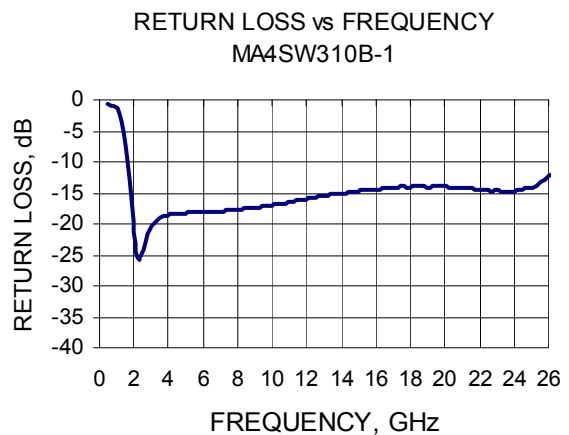
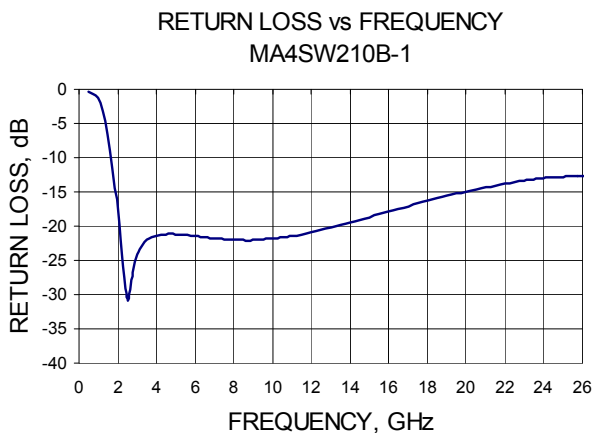
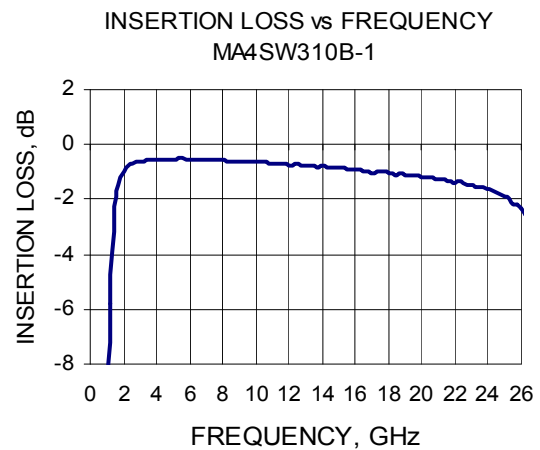
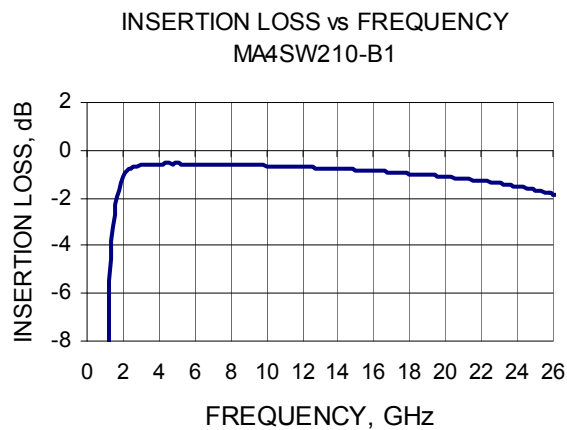
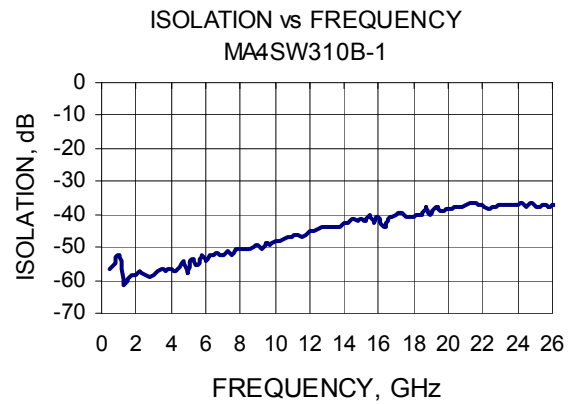
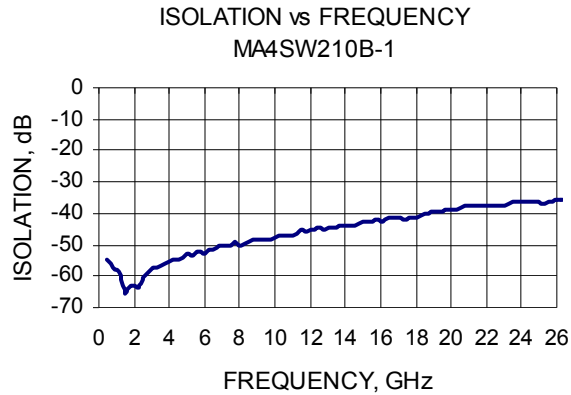
MA4SW310B-1 (SP3T)
Electrical Specifications @ T_{AMB} = +25°C, 20mA Bias current

Parameter	Frequency	Minimum	Nominal	Maximum	Units
Insertion Loss	2 GHz		1.6	2.0	dB
	6 GHz		0.8	1.1	dB
	12 GHz		1.0	1.3	dB
	18 GHz		1.3	1.9	dB
Isolation	2 GHz	54	59		dB
	6 GHz	47	50		dB
	12 GHz	40	45		dB
	18 GHz	36	40		dB
Input Return Loss	2 GHz		14		dB
	6 GHz		15		dB
	12 GHz		16		dB
	18 GHz		14		dB
Switching Speed¹	-		50		ns

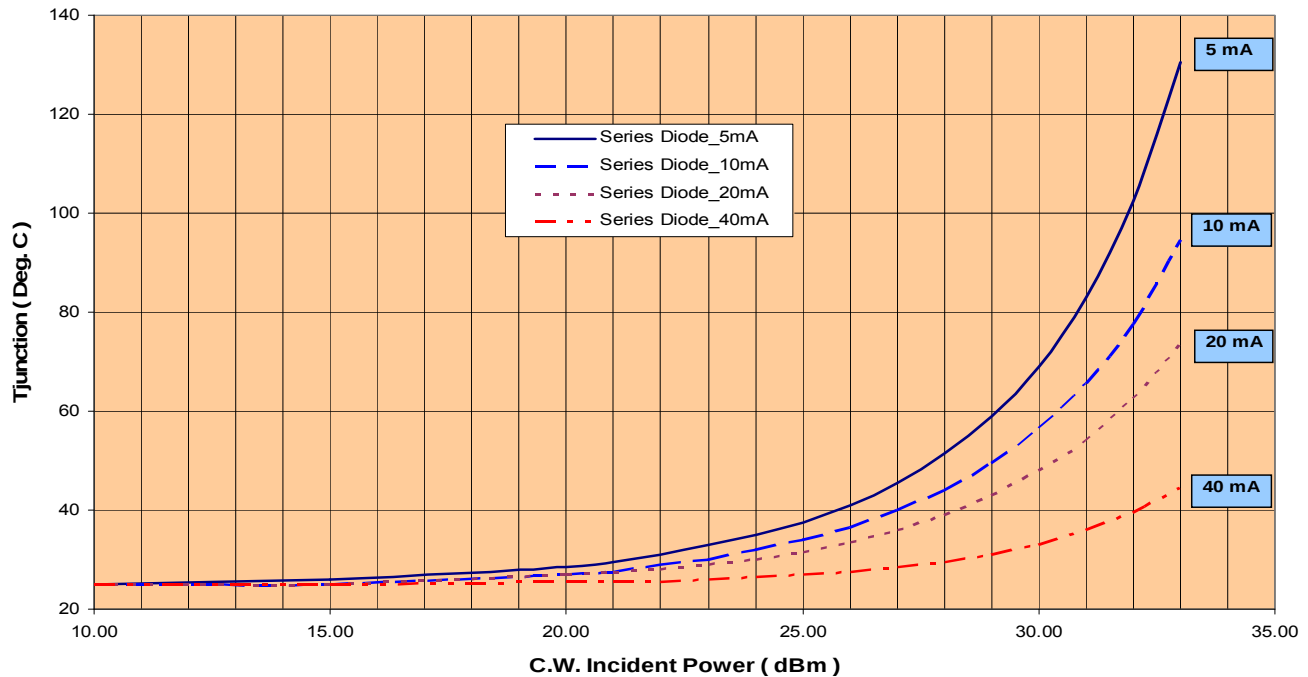
Note:

1. Typical switching speed measured from 10% to 90% of detected RF signal driven by TTL compatible drivers using RC output spiking network, R = 50 – 200Ω , C = 390 – 560pF.

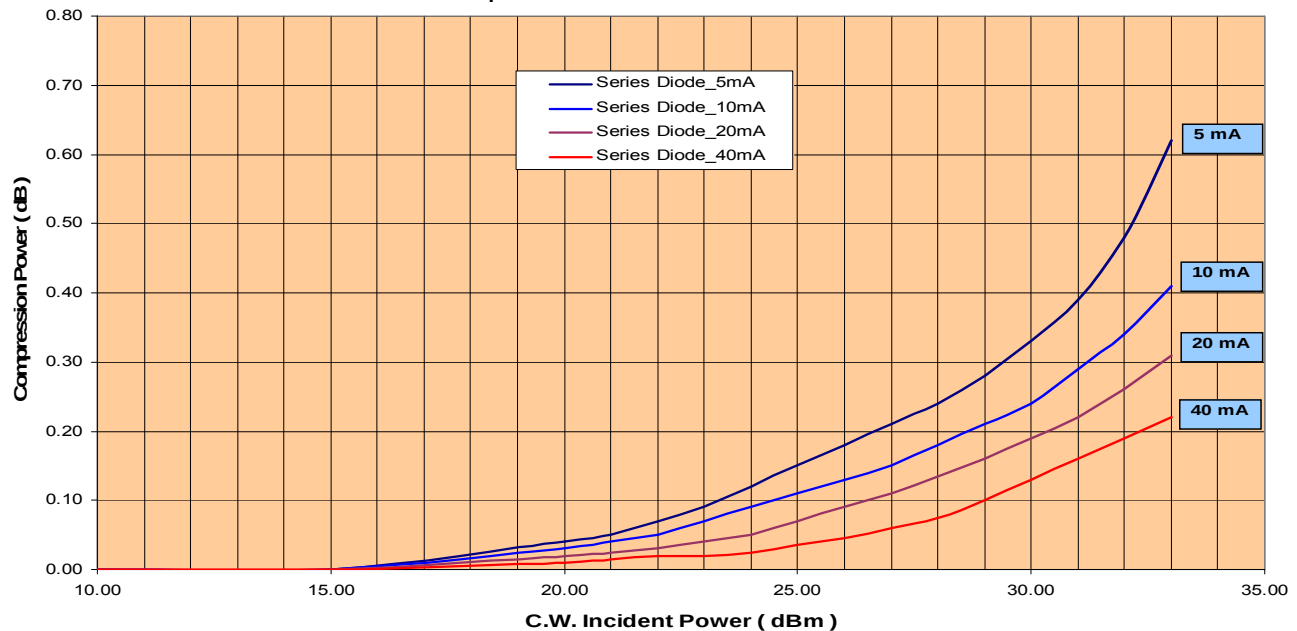
Typical RF Performance at $T_{AMB} = +25^{\circ}\text{C}$, 20mA Bias Current



MA4SW210B-1 Series Diode Junction Temperature vs. Incident Power at 8 GHz



MA4SW210B-1 Compression Power vs. Incident Power at 8 GHz



Note:

The MA4SW310B-1 contains the same PIN diodes and will have similar performance.

Operation of the MA4SW 210B-1 and MA4SW310B-1

Operation of the MA4SW210B-1 and MA4SW310B-1 PIN diode switches is achieved by simultaneous application of DC currents to the bias pads. The required levels for the different states are shown in the tables below. The control currents should be supplied by constant current sources. The nominal 40Ω - 60Ω pull-up resistor voltage @ J4 and J5 is usually -1V for -20mA and +20mA for +1V.

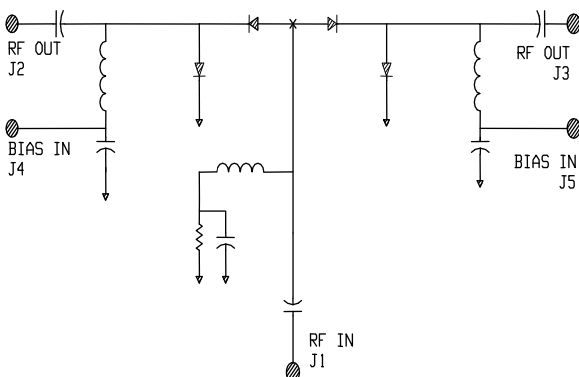
Driver Connections MA4SW210B-1

Control Level I_{DC} @		Condition of RF Output	Condition of RF Output
J4	J5	J1 - J2	J1 - J3
-20mA	+20mA	Low Loss	Isolation
+20mA	-20mA	Isolation	Low Loss

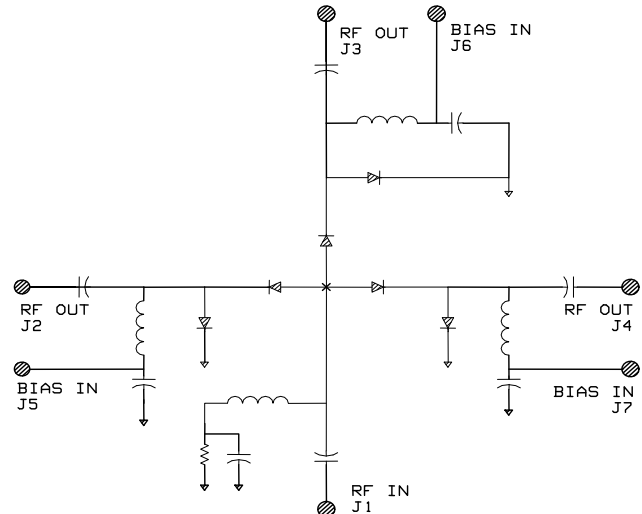
Driver Connections MA4SW310B-1

Control Level I_{DC} @			Condition of RF Output	Condition of RF Output	Condition of RF Output
J5	J6	J7	J1 - J2	J1 - J3	J1 - J4
-20mA	+20mA	+20mA	Low Loss	Isolation	Isolation
+20 mA	-20mA	+20mA	Isolation	Low Loss	Isolation
+20mA	+20mA	-20mA	Isolation	Isolation	Low Loss

Equivalent Circuit MA4SW210B-1



Equivalent Circuit MA4SW310B-1



Wire Bonding

Thermosonic wedge bonding using 0.003" x 0.00025" ribbon or 0.001" diameter gold wire is recommended. A heat stage temperature of 150°C and a force of 18 to 22 grams should be used. If ultrasonic energy is necessary, it should be adjusted to the minimum level required to achieve a good bond. RF bond wires should be kept as short as possible.

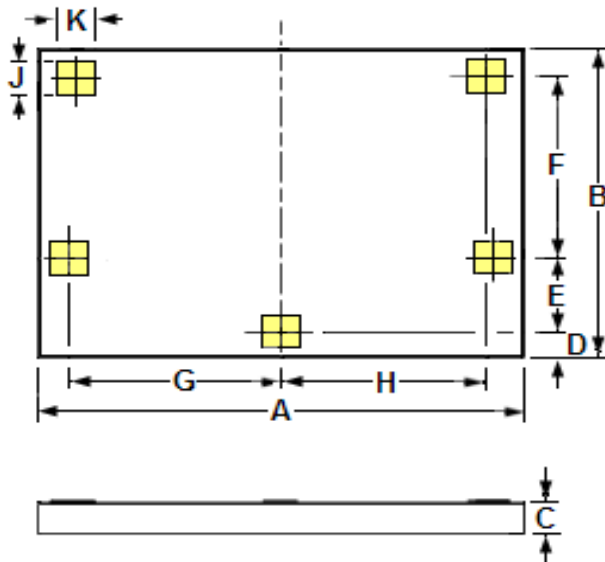
Chip Mounting

The HMIC switches have Ti-Pt-Au back metal. They can be die mounted with a gold-tin eutectic solder preform or conductive epoxy. Mounting surface must be clean and flat.

Eutectic Die Attachment: An 80/20, gold-tin, eutectic solder preform is recommended with a work surface temperature of 255°C and a tool tip temperature of 265°C. When hot gas is applied, the temperature at the chip should be 290°C. The chip should not be exposed to temperatures greater than 320°C for more than 20 seconds. No more than three seconds should be required for attachment. Solders rich in tin should not be used.

Epoxy Die Attachment: A minimum amount of epoxy, 1-2 mils thick, should be used to attach chip. A thin epoxy fillet should be visible around the outer perimeter of the chip after placement. Cure epoxy per product instructions. Typically 150°C for 1 hour.

MA4SW210B-1 Chip Outline^{1,2} & Dimensions



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.066	0.070	1.680	1.780
B	0.048	0.052	1.230	1.330
C	0.004	0.006	0.100	0.150
D	0.004	0.006	0.090	0.140
E	0.012	0.013	0.292	0.317
F	0.029	0.030	0.735	0.760
G	0.030	0.031	0.766	0.791
H	0.029	0.030	0.732	0.757
J	0.005	REF.	0.129	REF.
K	0.005	REF.	0.129	REF.

Notes:

1. Topside and backside metallization is gold, 2.5µm thick typical.
2. Yellow areas indicate wire bonding pads

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

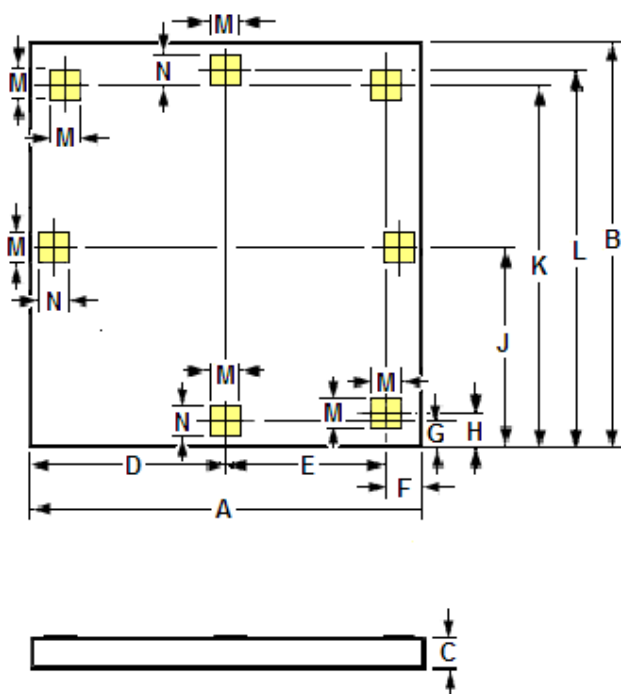
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Visit www.macomtech.com for additional data sheets and product information.

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MA4SW310B-1 Chip Outline^{1,2} & Dimensions



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.0697	0.0736	1.770	1.870
B	0.0693	0.0732	1.760	1.860
C	0.0039	0.0059	0.100	0.150
D	0.0310	0.0319	0.787	0.812
E	0.0289	0.0299	0.734	0.759
F	0.0055	0.0075	0.140	0.190
G	0.0035	0.0055	0.089	0.139
H	0.0044	0.0064	0.113	0.163
J	0.0338	0.0358	0.859	0.909
K	0.0632	0.0652	1.610	1.660
L	0.0660	0.0680	1.680	1.730
M	0.0051	REF.	0.1290	REF.
N	0.0046	REF.	0.1180	REF.

Notes:

1. Topside and backside metallization is gold , 2.5µm thick typical.
2. Yellow areas indicate wire bonding pads

Ordering Information

Part Number	Package
MA4SW210B-1	Gel Pack
MA4SW310B-1	Gel Pack